Who We Are

• We are a well-established, entrepreneurial business with an industry-leading team and a profitable business.

• We have spent nearly 30 years as part of Cree Inc., building the future with market-leading wide bandgap semiconductor products for the transportation, industrial, energy and communications markets.

• From young and ambitious roots in North Carolina’s Research Triangle Park, we have grown into a world-renowned commercial supplier of the fastest, most advanced wide bandgap semiconductor components and substrates available, enabling greater efficiency and performance, smaller systems and lower costs.

• **Our Mission:** lead the innovation and commercialization of SiC and GaN, liberating designers to invent power and wireless systems for a responsible, energy efficient future.

• **Our Vision:** *Powering More. Consuming Less.*

Products and Services

• SiC MOSFETs, Modules and Diodes

• GaN HEMTs and MMIC Amplifiers

• Substrates for SiC and GaN-on-SiC power and RF power devices

• GaN-on-SiC Foundry: custom GaN HEMT MMICs, including high-power amplifiers, LNA, switches and phase shifters

• Custom or pre-release SiC power products
Who We Serve

Communications

• MILCOM (Secure communications: handheld, man-pack, portable, vehicular, emergency services)
• SATCOM (Comms: video, Internet, voice)
• Radar (Weather, ATC, surveillance, marine)
• Telecom (4G LTE, Secure HD broadcast, CATV)

Transportation

• Automotive (EV traction motor)
• EV/HEV (On-board, offboard charging, on-board DC/DC converters)
• Traction (On-board train auxiliary power converters, air conditioning, signage, user power)

Energy

• Solar (PV string inverters, DC optimizers, micro inverters, central inverters)
• Grid (HV utility power conversion)
• Energy Storage (Battery chargers, energy back up systems)
• Wind (Inverters)

Industrial

• Motor (AFE regenerative drives)
• Power Supply Units
• IT Power Supplies (Servers, cloud data centers)
• UPS (High-frequency)
• Welding (Plasma welders)
• Induction Heating (High-frequency hardening/softening)
Technology Leadership

- Headquartered in Research Triangle Park, North Carolina, USA, with approximately 500 employees across nine locations on three continents

- 46,000 sq. ft. of fabrication and office facilities on 55 acres with Class 10, 100, 1000 and 10,000 clean rooms

- Accredited as a Category 1A trusted foundry by the U.S. Department of Defense

1STs

- 1991: Released world’s first commercial SiC wafers
- 1998: GaN HEMT on SiC
- 1999: Demonstrated 4-inch SiC wafer
- 2000: MMIC in GaN
- 2006: 1200V SiC Schottky Diode
- 2007: Commercial release of 100-mm, zero-micropipe SiC substrates
- 2008: Release of 90W GaN HEMT
- 2009: Record-efficiency GaN HEMT Doherty Amplifier with Digital Predistortion
- 2010: 1700V SiC Schottky Diode
- 2010: Developed high-quality 150-mm SiC substrates
- 2011: 1200V SiC 80mΩ MOSFET
- 2012: 1200V SiC half-bridge module
- 2014: 1700V SiC half-bridge module
- 2014: 1200V SiC 25mΩ MOSFET
- 2015: 900V SiC MOSFET
- 2015: Demonstrated 200-mm SiC wafer
- 2016: 1000V SiC MOSFET
- 2016: Released market’s highest-power, single-ended transistor for L-Band Radar
- 2017: Industry’s lowest figure-of-merit SiC MOSFET

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3.8 Trillion

Total Field Hours for Wolfspeed SiC and GaN Products

15 Billion

Kilowatt Hours of Electricity that would be Saved Annually if Every Data Center Worldwide Upgraded to SiC

171 Million

Dollars of Revenue (Including Wolfspeed Materials) Earned in Fiscal 2016

2245

Patents Held and Pending by Wolfspeed

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